Atty. Dkt. No. 035905-0104

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Thomas H. LEE et al.

Title: DENSE ARRAYS AND CHARGE STORAGE DEVICES AND METHODS FOR MAKING SAME

Appl. No.: 09/927,648

Filing Date: August 13, 2001

Examiner: Unassigned

Art Unit: 2818

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.56

Commissioner for Patents
Washington, D.C. 20231

Sir:

Submitted herewith on Form PTO-1449 is a listing of documents known to Applicants in order to comply with Applicants' duty of disclosure pursuant to 37 CFR §1.56. A copy of each listed document is being submitted to comply with the provisions of 37 CFR §1.97 and §1.98.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

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TIMING OF THE DISCLOSURE

The listed documents are being submitted in compliance with 37 CFR §1.97(b), before the mailing of the first official action.

RELEVANCE OF EACH DOCUMENT

All of the documents are in English.

Applicants respectfully request that any listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO-1449 be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 06-1447. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 06-1447.

Respectfully submitted,

Date: 11/27/01

By _____

Leon Radomsky
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Sheet 1 of 7

Complete if Known	
Application Number	09/927,648
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Group Art Unit	2818
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Attorney Docket Number	035905/0104

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A51	5,427,979		Chang	6/27/1995	
	A52	5,070,384		McCollum et al.	12/3/1991	
	A53	4,498,226		Inoue et al.	2/12/1985	
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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Attorney Docket Number	035905/0104

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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